

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ Max}$	I_D $T_C = +25^\circ\text{C}$
100V	140m Ω @ $V_{GS} = 10\text{V}$	12A
	160m Ω @ $V_{GS} = 4.5\text{V}$	11A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Analog Switch

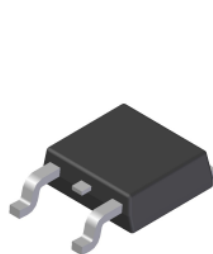
Features

- Low On-Resistance
- Low Input Capacitance
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

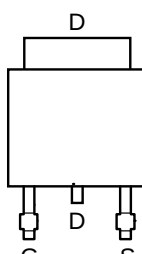
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe.
Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.33 grams (Approximate)

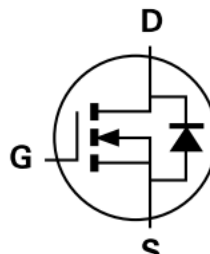
TO252 (DPAK)



Top View



Top View



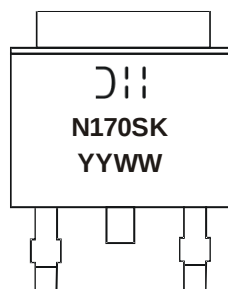
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN10H170SK3-13	TO252 (DPAK)	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



D = Manufacturer's Marking
 N170SK = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Digit of Year (ex: 15 = 2015)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	100	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	T _C = +25°C	I _D	12	A
		T _C = +100°C		7.5	
Maximum Body Diode Forward Current (Note 5)			I _S	4	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	16	A
Avalanche Current (Note 6)			I _{AS}	5.3	A
Avalanche Energy (Note 6)			E _{AS}	20	mJ

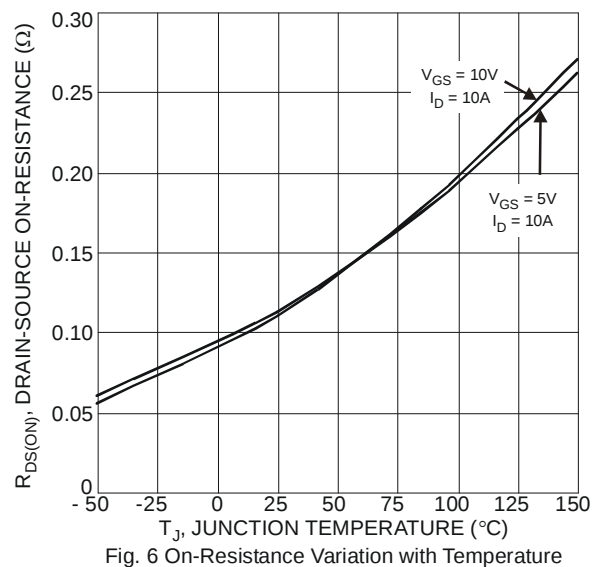
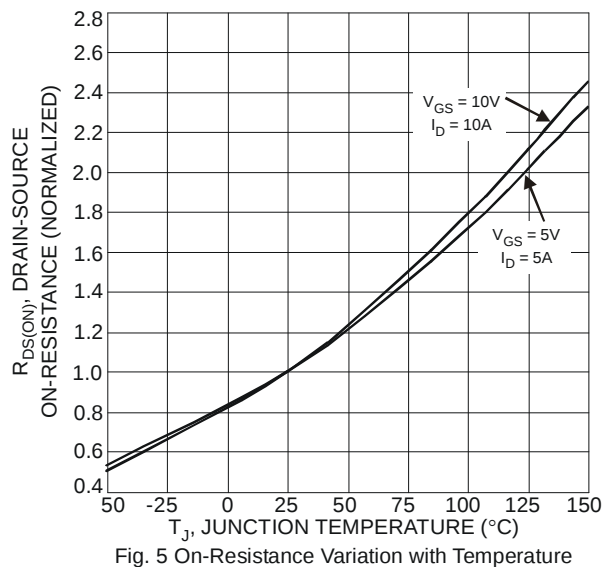
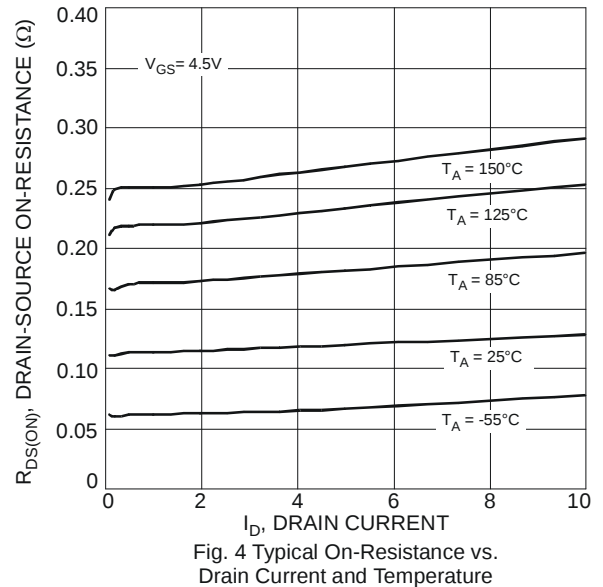
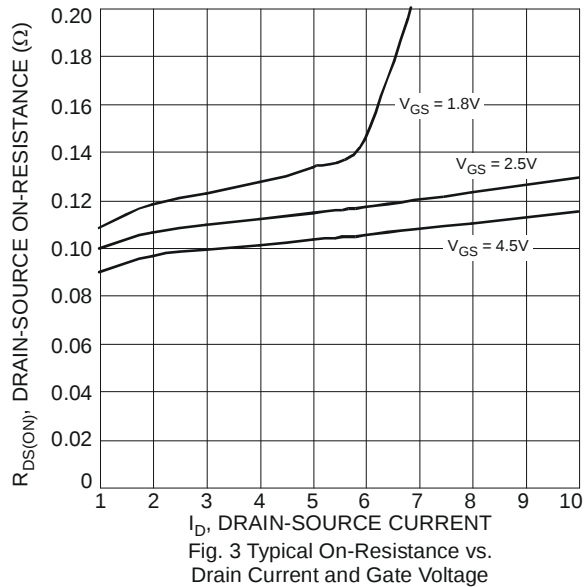
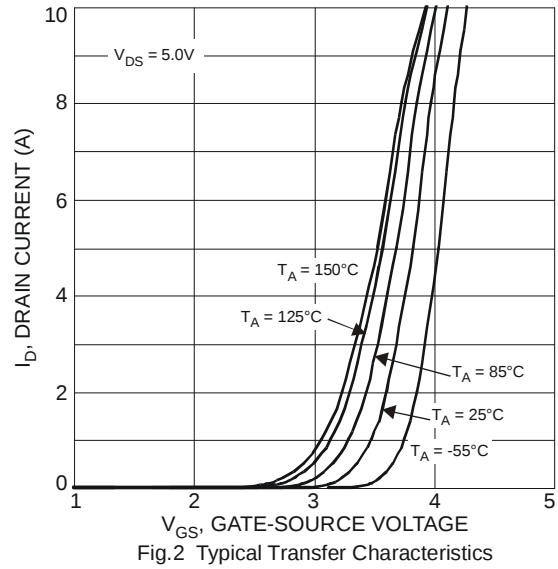
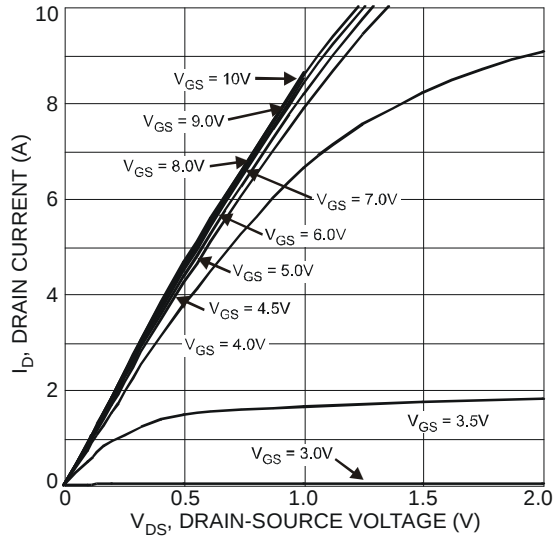
Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _C = +25°C	P _D	42	W
	T _C = +100°C		17	
Thermal Resistance, Junction to Ambient (Note 5)		R _{θJA}	44	°C/W
Thermal Resistance, Junction to Case (Note 5)		R _{θJC}	3	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 100V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	1.0	2.0	3.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	99	140	mΩ	V _{GS} = 10V, I _D = 5A
		—	104	160		V _{GS} = 4.5V, I _D = 5A
Diode Forward Voltage	V _{SD}	—	0.7	1.0	V	V _{GS} = 0V, I _S = 10A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	1,167	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{OSS}	—	36	—		
Reverse Transfer Capacitance	C _{RSS}	—	25	—		
Gate Resistance	R _G	—	1.3	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	4.9	—	nC	V _{DS} = 80V, I _D = 12.8A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	9.7	—		
Gate-Source Charge	Q _{gs}	—	2.0	—		
Gate-Drain Charge	Q _{gd}	—	2.0	—	nS	V _{DD} = 50V, R _G = 25Ω, I _D = 12.8A
Turn-On Delay Time	t _{D(on)}	—	10.5	—		
Turn-On Rise Time	t _r	—	11.1	—		
Turn-Off Delay Time	t _{D(off)}	—	42.6	—		
Turn-Off Fall Time	t _f	—	12.8	—	nS	V _{GS} = 0V, I _S = 12.8A, dI/dt = 100A/μs
Body Diode Reverse Recovery Time	t _{rr}	—	30.3	—		
Body Diode Reverse Recovery Charge	Q _{rr}	—	35.2	—	nC	V _{GS} = 0V, I _S = 12.8A, dI/dt = 100A/μs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper pad layout.
 - UIS in production with L = 1.43mH, T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design; not subject to production testing.



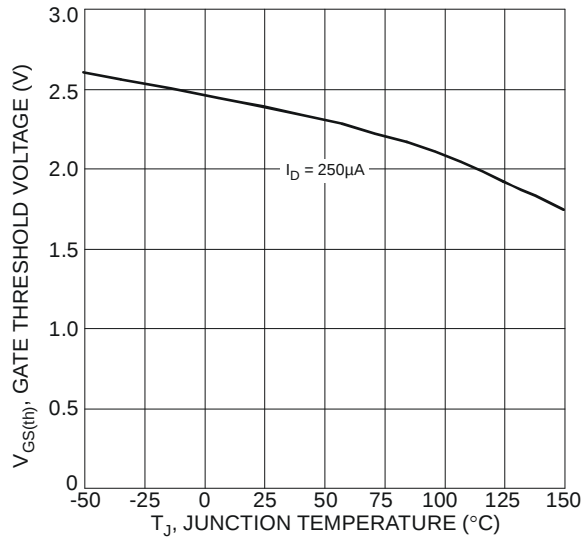


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

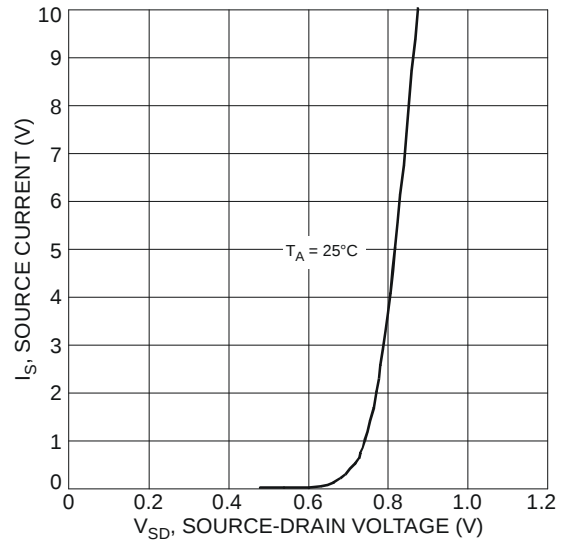


Fig.8 Diode Forward Voltage vs. Current

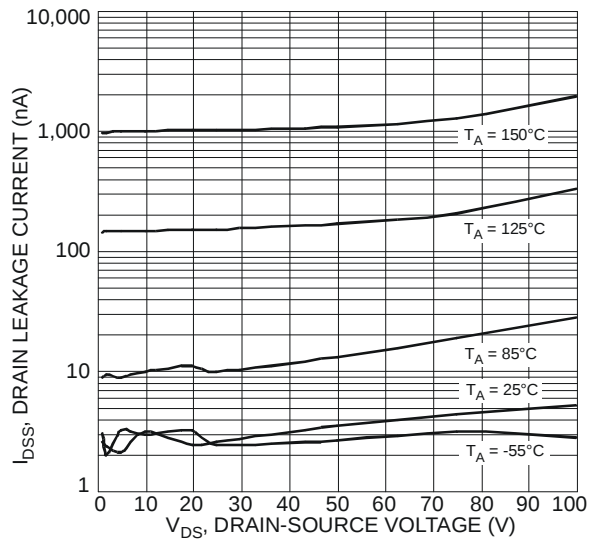


Fig. 9 Typical Drain-Source Leakage Current vs. Voltage

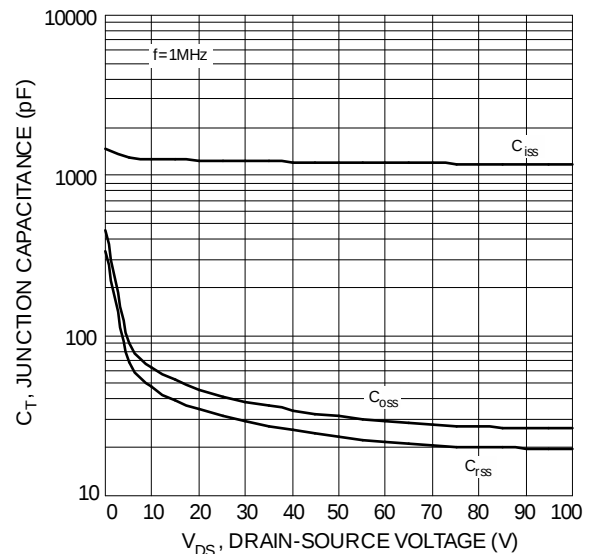


Figure 10 Typical Junction Capacitance

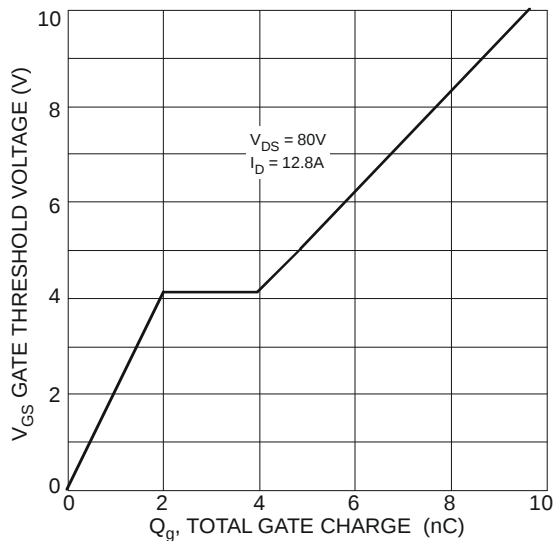


Fig. 11 Gate Charge

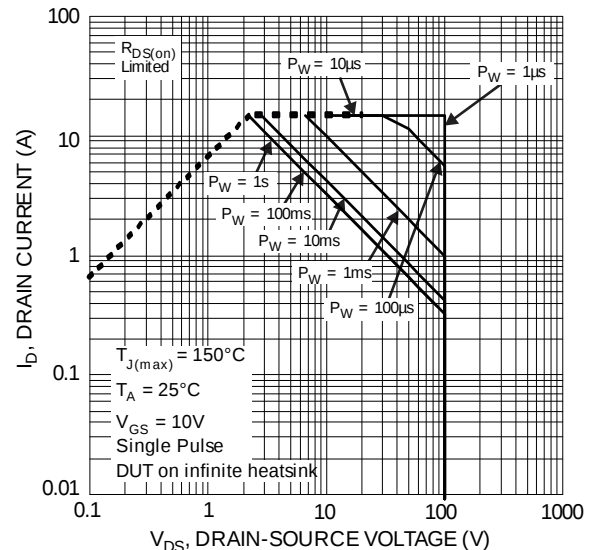
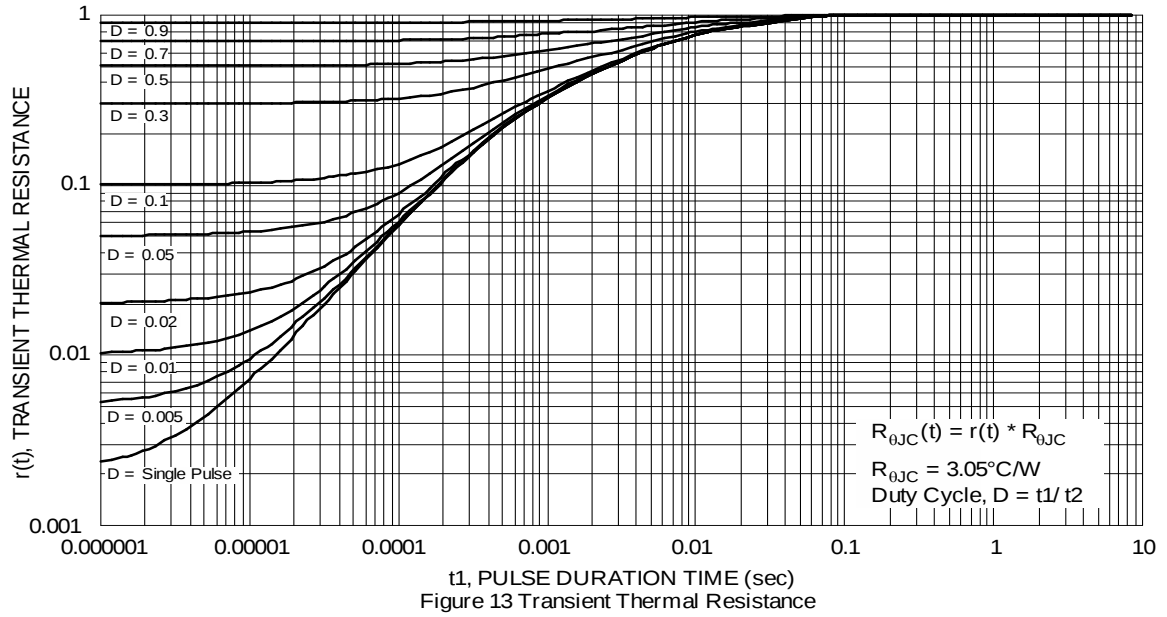


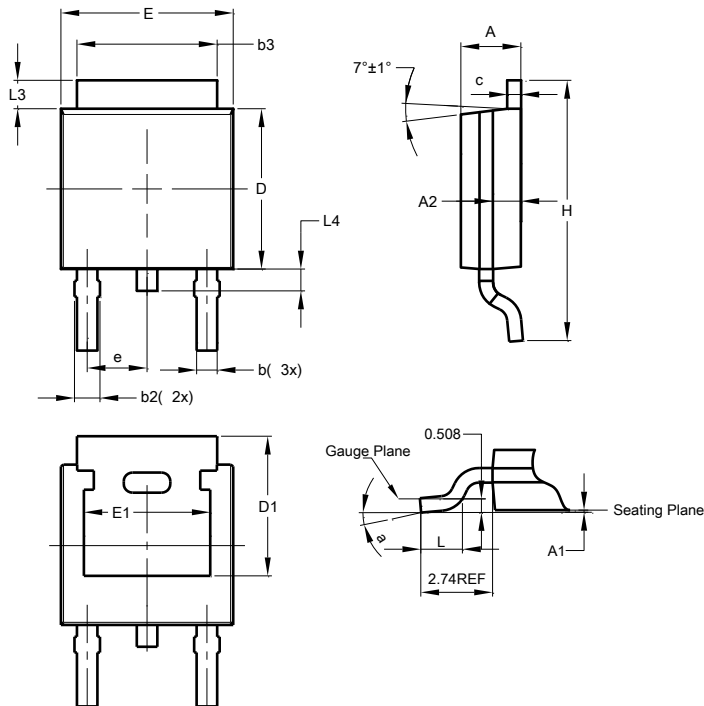
Figure 12 SOA, Safe Operation Area



Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

TO252 (DPAK)

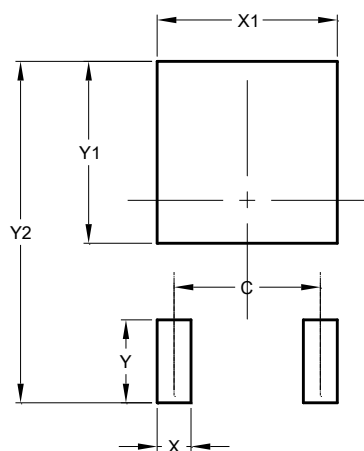


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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